Thyristors Datasheet

Po



Additional Information





<u>S</u>



Resources

Accessories

Samples

Description

Designed primarily for full-wave ac control applications, such as motor controls, heating controls and power supplies; or wherever half–wave silicon gate–controlled, solid–state devices are needed.

Features

- Glass Passivated Junctions and Center Gate Fire for Greater Parameter Uniformity and Stability
- Blocking Voltage to 50 Volts
- This is a Pb-Free Device
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability

Functional Diagram



Pin Out



Maximum Ratings (TJ = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, T _J = 25° to 100°C)	V _{drm} , V _{rrm}	50	V
On-State RMS Current (180° Conduction Angles; $T_c = 75$ °C)	I _{T (RMS)}	8.0	А
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, $T_c = 75^{\circ}$ C)	I	90	А
Circuit Fusing Consideration (t = 8.3 ms)	l²t	34	A ² sec
Forward Peak Gate Power (Pulse Width = 10 μ s, T _c = 70°C)	P _{GM}	5.0	W
Forward Average Gate Power (t = 8.3 ms, $T_c = 70^{\circ}$ C)	P _{G (AV)}	0.5	W
Forward Peak Gate Current (Pulse Width = 10 s, $T_c = 70^{\circ}$ C)	I _{GM}	2.0	W
Operating Junction Temperature Range	T	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the

Recommended Operating Conditions may affect device reliability. 1. V_{DBM} and V_{BBM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Thermal Characteristics

Rating		Symbol	Value	Unit
Thermal Resistance	Junction-to-Case (AC) Junction-to-Ambient	R _{sjc} R _{sja}	1.8 62.5	°C/W
Maximum Lead Temperature for Soldering Purpose	s, 1/8" from case for 10 seconds	T,	260	°C

Electrical Characteristics - OFF (TC = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
†Peak Repetitive Blocking Current	T_ = 25°C	I _{DRM} ,	-	-	10	μΑ
$(V_{AK} = V_{DRM} = V_{RRM}; \text{ Gate Open})$	T_ = 125°C	I	-	-	0.5	mA

Electrical Characteristics - ON (TC = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak On–State Voltage (Note 2) (I_{TM} = 16 A Peak, T_{C} = 25°C)		V _{TM}	_	-	1.83	V
Gate Trigger Current (Continuous dc)	$T_c = 25^{\circ}C$	I	_	-	25	mA
$(V_{AK} = 12 \text{ V}, \text{ R}_{L} = 100 \Omega)$	$T_c = -40^{\circ}C$	GT	-	-	40	ША
Gate Trigger Voltage (Continuous dc)	$T_c = 25^{\circ}C$	V	-	-	1.5	V
$(V_{AK} = 12 \text{ V}, \text{ R}_{L} = 100 \Omega)$	$T_c = -40^{\circ}C$	V _{gt}	-	-	2.0	v
Gate Non-Trigger Voltage (Continuous dc) $(V_{AK} = 12 \text{ V}, \text{ R}_{L} = 100 \Omega, \text{ T}_{c} = 125^{\circ}\text{C})$		V_{GD}	0.2	-	_	
Holding Current	$T_c = 25^{\circ}C$	V	-	-	30	mA
$(V_{D} = 12 \text{ V}, \text{ Gate Open}, \text{ Initiating Current} = 200 \text{ mA})$	$T_c = -40^{\circ}C$	V_{GD}	-	-	60	ША
Turn-Of f Time (V_{D} = Rated V_{DRM}) (I_{TM} = 8 A, I_{R} = 8 A)		t _q	-	30	_	μS

2. Indicates Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.

Dynamic Characteristics

Characteristic	Symbol	Min	Тур	Max	Unit
Critical Rate of Rise of Off-State Voltage ($V_D = 0.66 \times V_{DRM'}$ Exponential Waveform, Gate Open, $T_J = 100^{\circ}$ C)	dV/dt	-	200	-	V/µs



Thyristors Datasheet

Voltage Current Characteristic of SCR

Symbol	Parameter
V _{drm}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
I _H	Holding Current



Figure 1. Current Derating (Half-Wave)



Figure 3. Maximum Power Dissipation (Half-Wave)



Figure 2. Current Derating (Full-Wave)







Thyristors Datasheet

Dimensions





Part Marking System



Dim	Inc	hes	Millin	neters
Dim	Min	Мах	Min	Max
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
К	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
Ν	0.195	0.205	4.95	5.21
٥	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
v	0.045	-	1.15	-
Z	-	0.080	-	2.04

Pin Assignment			
1	Cathode		
2	Anode		
3	Gate		
4	Anode		

Ordering Information

Device	Package	Shipping
C122F1G	TO-220AB (Pb-Free)	1000 Units / Box

1. Dimensioning and tolerancing per ansi y14.5m, 1982.

Controlling dimension: inch.
 Dimension z defines a zone where all body and lead irregularities are allowed.

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at http://www.littelfuse.com/disclaimer-electronics.



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for SCRs category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below :

 NTE5428
 T1500N16TOF VT
 TT162N16KOF-A
 TT162N16KOF-K
 TT330N16AOF
 VS-22RIA20
 VS-2N685
 057219R
 T1190N16TOF VT

 T1220N22TOF VT
 T201N70TOH
 T700N22TOF
 T830N18TOF
 TT250N12KOF-K
 VS-16RIA120
 VS-110RKI40
 NTE5427
 NTE5442

 TT251N16KOF-K
 VS-22RIA100
 VS-16RIA40
 TD250N16KOF-A
 VS-ST110S16P0
 T930N36TOF VT
 T2160N24TOF VT
 T1190N18TOF

 VT
 T1590N28TOF VT
 2N1776A
 T590N14TOF
 NTE5375
 NTE5460
 NTE5481
 NTE5512
 NTE5518
 NTE5519
 NTE5529

 NTE5553
 NTE5557
 NTE5567
 NTE5570
 NTE5572
 NTE5576
 NTE5578
 NTE5579
 NTE5592
 NTE5598